

Listing of the Claims

Please cancel claim 2 without prejudice.

1. - 27. (Cancelled)

28. (Original) A semiconductor structure of a damascene or dual damascene interconnect formed by a trench-filling process of electroplated Cu having an as-deposited grain size of not less than $0.5\ \mu\text{m}$ and a decrease in electrical resistance of at least 15% after a time period of not more than 30 hours at about 21°C .

29. (Original) A semiconductor structure of a damascene or dual damascene interconnect according to claim 28, wherein said as-deposited grain size of electroplated Cu is between about $0.5\ \mu\text{m}$ and about $.15\ \mu\text{m}$.

30. (Original) A semiconductor structure of a damascene or dual damascene interconnect according to claim 28, wherein said grain size of said electroplated Cu after said time period of not more than 30 hours at about 21°C is between about $1.5\ \mu\text{m}$ and about $2\ \mu\text{m}$.